# Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs

# **High-Performance Silicon-Gate CMOS**

The MC74HCT574A is identical in pinout to the LS574. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HCT574A is identical in function to the HCT374A but has the flip—flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

## **Features**

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

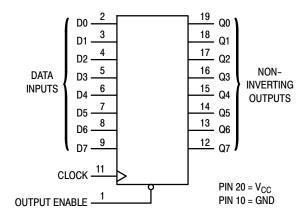


Figure 1. Logic Diagram



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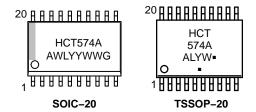


SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

#### **PIN ASSIGNMENT**

OUTPUT					
ENABLE	þ	1 •	20	Ь	$V_{CC}$
D0	þ	2	19	þ	Q0
D1	þ	3	18	þ	Q1
D2	þ	4	17	þ	Q2
D3	þ	5	16	þ	Q3
D4	d	6	15	Ь	Q4
D5	þ	7	14	þ	Q5
D6	d	8	13	þ	Q6
D7	d	9	12	Ь	Q7
GND	d	10	11	þ	CLOCK

#### **MARKING DIAGRAMS**



A = Assembly Location WL, L = Wafer Lot

YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

## **FUNCTION TABLE**

	Inputs	Output	
OE	Clock	D	Q
L		Н	Н
L		L	L
L	L,H, ∕_	X	No Change
Н	X	Х	Z

X = don't careZ = high impedance

# **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

Design Criteria	Value	Units
Internal Gate Count*	71.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рЈ

<sup>\*</sup>Equivalent to a two-input NAND gate.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package†	500	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs (SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 2)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

<sup>†</sup>Derating: SOIC Package: -7 mW/°C from 65° to 125°C

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	Guaranteed Limit		
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	V
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
I <sub>OZ</sub>	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH} \text{ (Note 1)}$ $V_{out} = V_{CC} \text{ or GND}$	5.5	-0.5	-5.0	-10	μΑ
$\Delta I_{CC}$	Additional Quiescent Supply Current	V <sub>in</sub> = 2.4 V, Any One Input V <sub>in</sub> = V <sub>CC</sub> or GND, Other Inputs		≥ <b>-55°C</b>	25°C to	125°C	
		$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2	.4	mA

<sup>1.</sup> Output in high-impedance state.

# AC ELECTRICAL CHARACTERISTICS (V<sub>CC</sub> = 5.0 V $\pm$ 10%, C<sub>L</sub> = 50 pF, Input $t_r$ = $t_f$ = 6.0 ns)

		Guaranteed Limit			
Symbol	Parameter	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f <sub>MAX</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5)	30	24	20	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Clock to Q (Figures 2 and 5)	30	38	45	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	28	35	42	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	Maximum Propagation Delay Time, Output Enable to Q (Figures 3 and 6)	28	35	42	ns
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output (Figures 2, 3 and 5)	12	15	18	ns
t <sub>THL</sub>					
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF

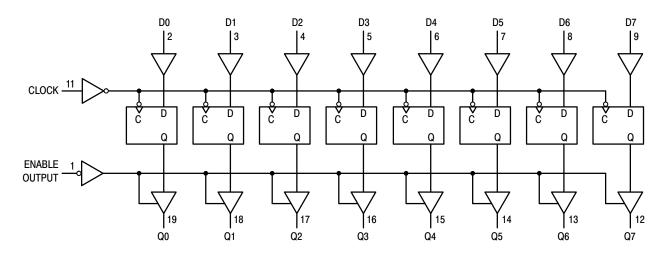
		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Flip–Flop)*	58	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

# **TIMING REQUIREMENTS** (V<sub>CC</sub> = 5.0 V $\pm 10\%$ , C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

			Guaranteed Limit						
			– 55 to	– 55 to 25°C		5°C	≤ 12	25°C	
Symbol	Parameter	Figure	Min	Max	Min	Max	Min	Max	Unit
t <sub>su</sub>	Minimum Setup Time, Data to Clock	4	10		13		15		ns
t <sub>h</sub>	Minimum Hold Time, Clock to Data	4	5.0		5.0		5.0		ns
t <sub>w</sub>	Minimum Pulse Width, Clock	2	15		19		22		ns
t <sub>r</sub> , If	Maximum Input Rise and Fall Times	2		500		500		500	ns

# **EXPANDED LOGIC DIAGRAM**



# **SWITCHING WAVEFORMS**

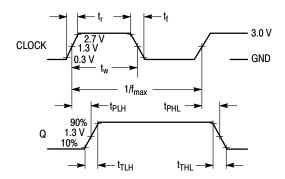


Figure 2.

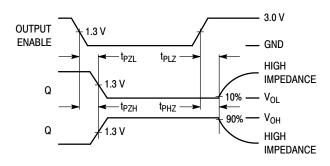


Figure 3.

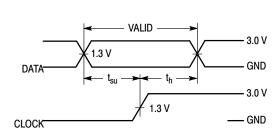
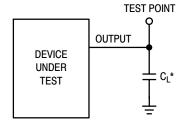


Figure 4.



\*Includes all probe and jig capacitance

Figure 5. Test Circuit

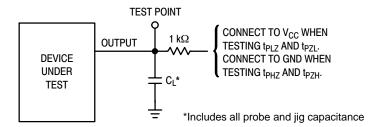


Figure 6. Test Circuit

# **ORDERING INFORMATION**

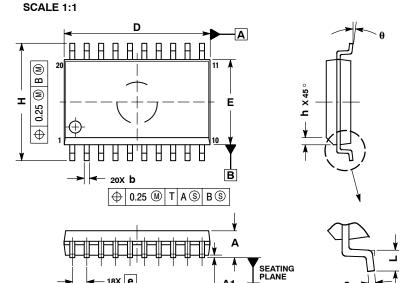
Device	Package	Shipping <sup>†</sup>
MC74HCT574ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HCT574ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HCT574ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOIC-20 WB CASE 751D-05 **ISSUE H** 

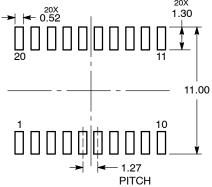
**DATE 22 APR 2015** 



- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

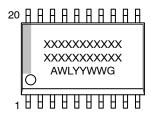
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

# **RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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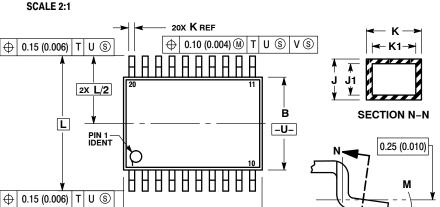
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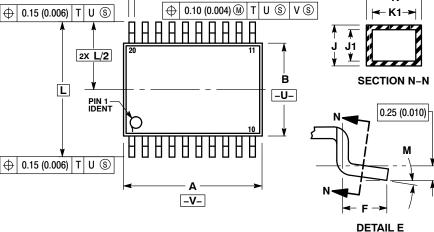
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

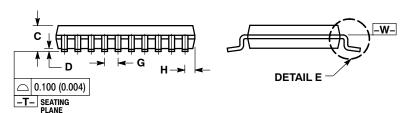


# TSSOP-20 WB CASE 948E ISSUE D

**DATE 17 FEB 2016** 







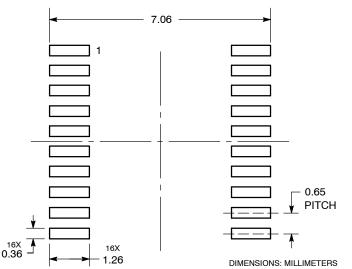
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

#### **GENERIC SOLDERING FOOTPRINT MARKING DIAGRAM\***



<u> </u>	_			
XXXX	1			
XXXX	L			
ALYW■	L			
• •	L			
<u> </u>				

= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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